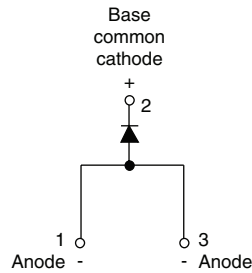


Fast Soft Recovery Rectifier Diode, 10 A



D²PAK (SMD-220)



FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition
- Designed and qualified for industrial level



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Output rectification and freewheeling in inverters, choppers and converters
- Input rectifications where severe restrictions on conducted EMI should be met

DESCRIPTION

The VS-10ETF..SPbF fast soft recovery rectifier series has been optimized for combined short reverse recovery time and low forward voltage drop.

The glass passivation ensures stable reliable operation in the most severe temperature and power cycling conditions.

PRODUCT SUMMARY

V_F at 10 A	< 1.33 V
t_{rr}	80 ns
V_{RRM}	1000 V/1200 V

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Sinusoidal waveform	10	A
V_{RRM}		1000/1200	V
I_{FSM}		160	A
V_F	10 A, $T_J = 25\text{ °C}$	1.33	V
t_{rr}	1 A, 100 A/ μ s	80	ns
T_J	Range	- 40 to 150	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} AT 150 °C mA
VS-10ETF10SPbF	1000	1100	4
VS-10ETF12SPbF	1200	1300	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	$T_C = 125\text{ °C}$, 180° conduction half sine wave	10	A
Maximum peak one cycle non-repetitive surge current	I_{FSM}	10 ms sine pulse, rated V_{RRM} applied	160	
		10 ms sine pulse, no voltage reapplied	185	
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	128	A ² s
		10 ms sine pulse, no voltage reapplied	180	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$, no voltage reapplied	1800	A ² \sqrt{s}

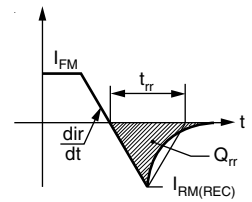
VS-10ETF..SPbF Soft Recovery Series



Vishay High Power Products Fast Soft Recovery Rectifier Diode, 10 A

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V_{FM}	10 A, $T_J = 25\text{ }^\circ\text{C}$		1.33	V
Forward slope resistance	r_t	$T_J = 150\text{ }^\circ\text{C}$		22.9	m Ω
Threshold voltage	$V_{F(TO)}$			0.96	V
Maximum reverse leakage current	I_{RM}	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}$	0.1	mA
		$T_J = 150\text{ }^\circ\text{C}$		4	

RECOVERY CHARACTERISTICS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Reverse recovery time	t_{rr}	I_F at 10 Apk 25 A/ μ s 25 $^\circ\text{C}$	310	ns
Reverse recovery current	I_{rr}		4.7	A
Reverse recovery charge	Q_{rr}		1.05	μC
Typical snap factor	S		0.6	



THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		- 40 to 150	$^\circ\text{C}$
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.5	$^\circ\text{C/W}$
Maximum thermal resistance, junction to ambient (PCB mount)	$R_{thJA}^{(1)}$		62	
Soldering temperature	T_S		240	$^\circ\text{C}$
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D ² PAK (SMD-220)	10ETF10S	
			10ETF12S	

Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μ m) copper 40 $^\circ\text{C/W}$. For recommended footprint and soldering techniques refer to application note #AN-994.

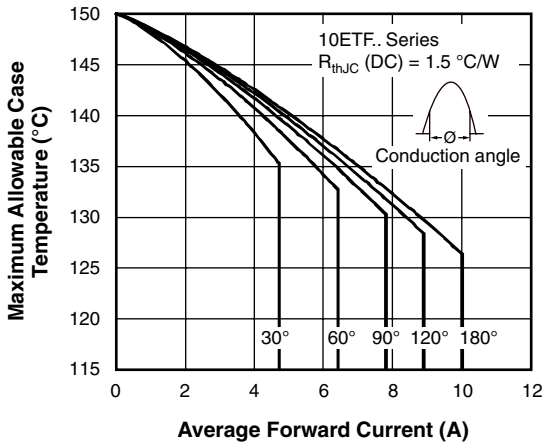


Fig. 1 - Current Rating Characteristics

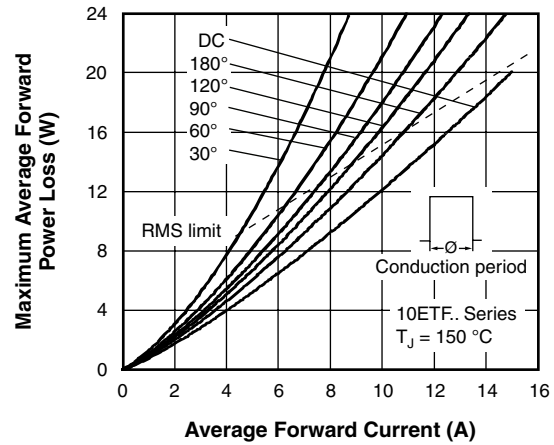


Fig. 4 - Forward Power Loss Characteristics

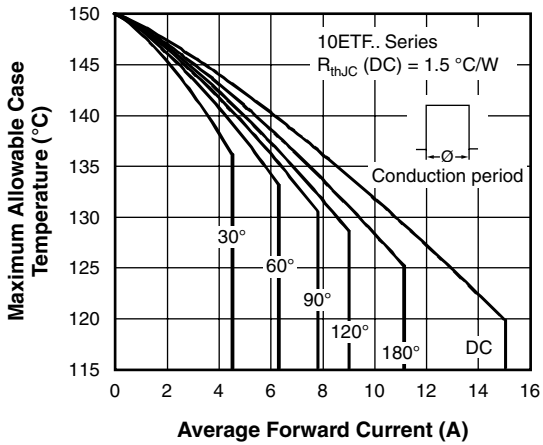


Fig. 2 - Current Rating Characteristics

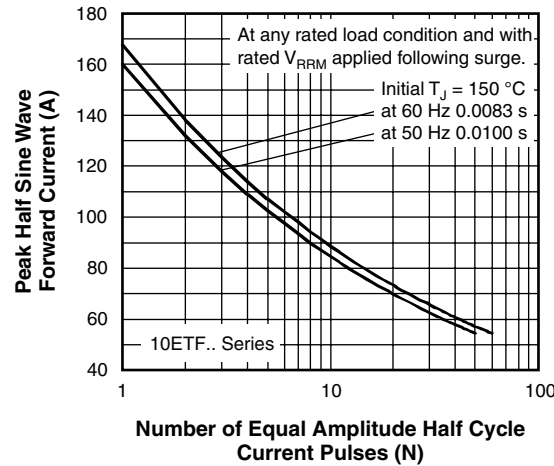


Fig. 5 - Maximum Non-Repetitive Surge Current

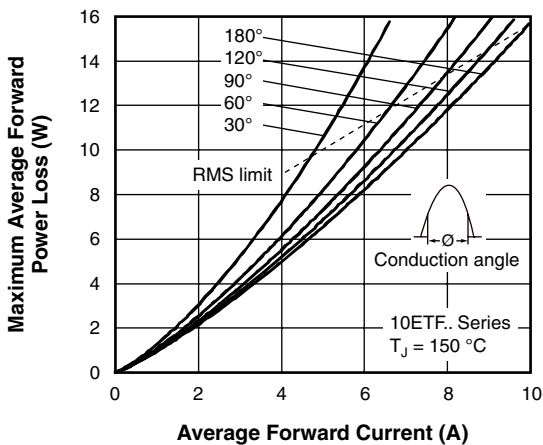


Fig. 3 - Forward Power Loss Characteristics

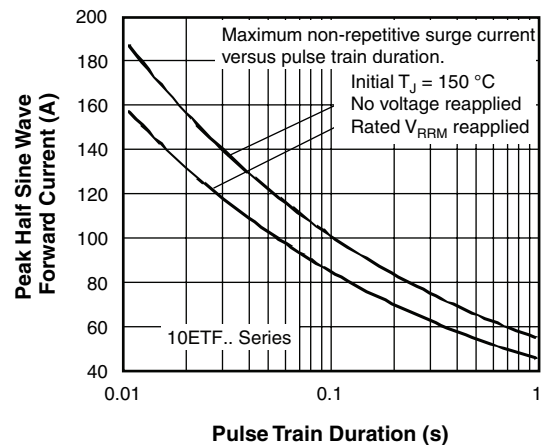


Fig. 6 - Maximum Non-Repetitive Surge Current

VS-10ETF..SPbF Soft Recovery Series



Vishay High Power Products Fast Soft Recovery Rectifier Diode, 10 A

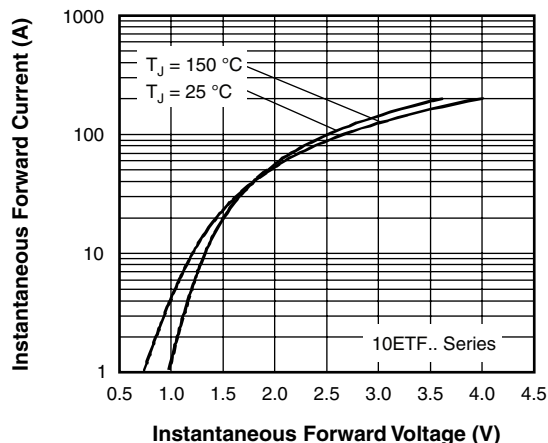


Fig. 7 - Forward Voltage Drop Characteristics

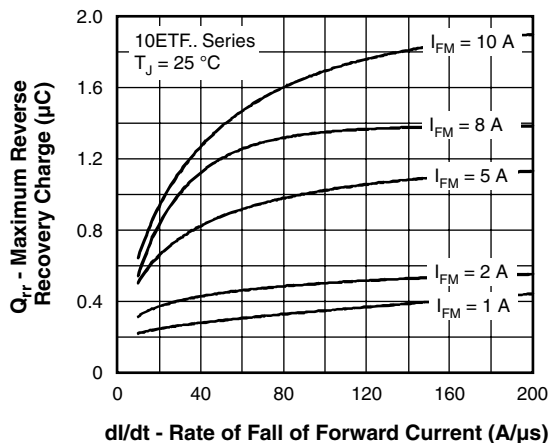


Fig. 10 - Recovery Charge Characteristics, $T_J = 25\text{ }^\circ\text{C}$

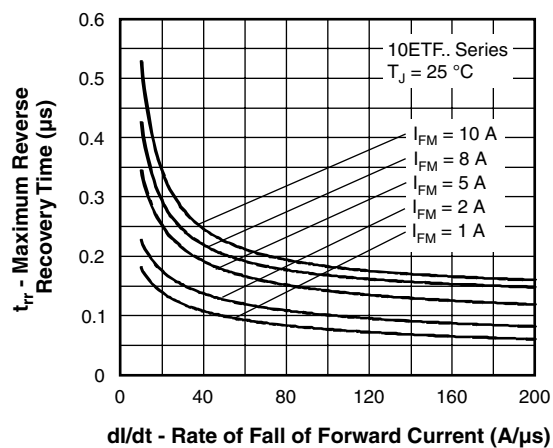


Fig. 8 - Recovery Time Characteristics, $T_J = 25\text{ }^\circ\text{C}$

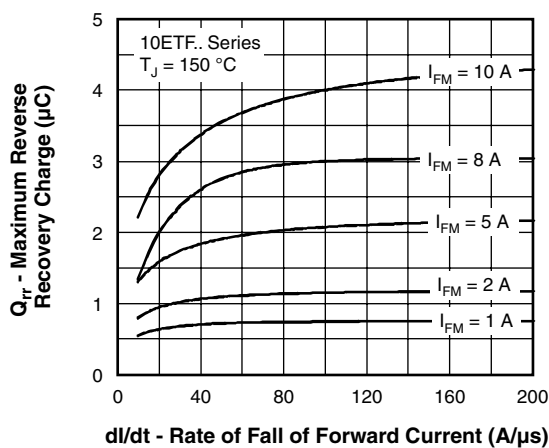


Fig. 11 - Recovery Charge Characteristics, $T_J = 150\text{ }^\circ\text{C}$

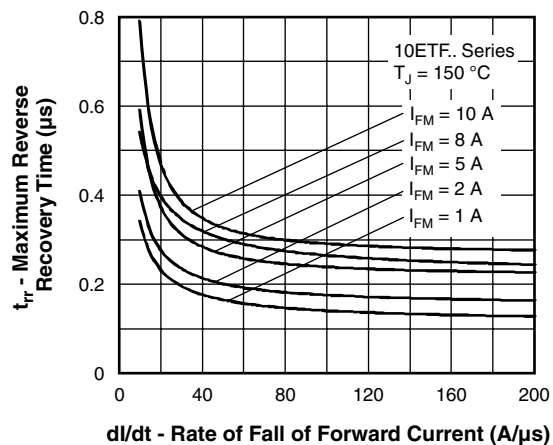


Fig. 9 - Recovery Time Characteristics, $T_J = 150\text{ }^\circ\text{C}$

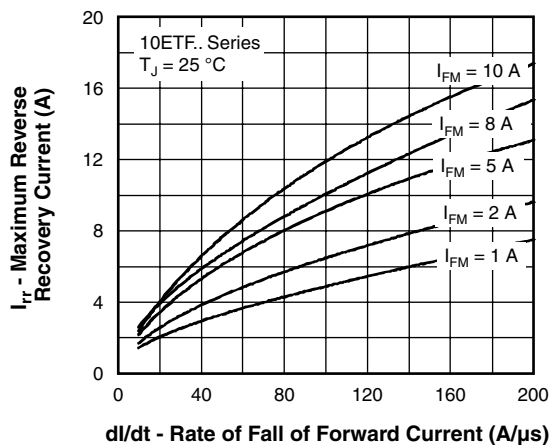


Fig. 12 - Recovery Current Characteristics, $T_J = 25\text{ }^\circ\text{C}$



VS-10ETF..SPbF Soft Recovery Series

Fast Soft Recovery Rectifier Diode, 10 A
Vishay High Power Products

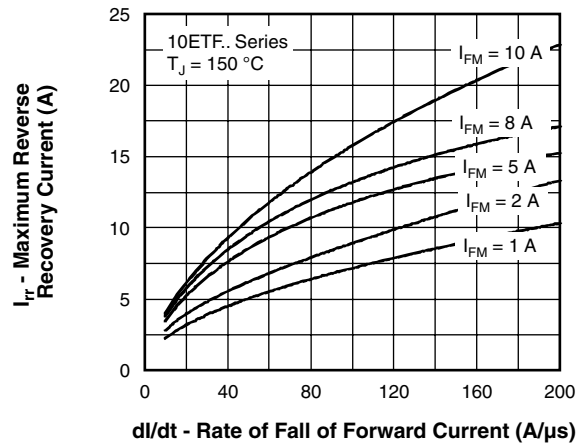


Fig. 13 - Recovery Current Characteristics, $T_J = 150\text{ }^\circ\text{C}$

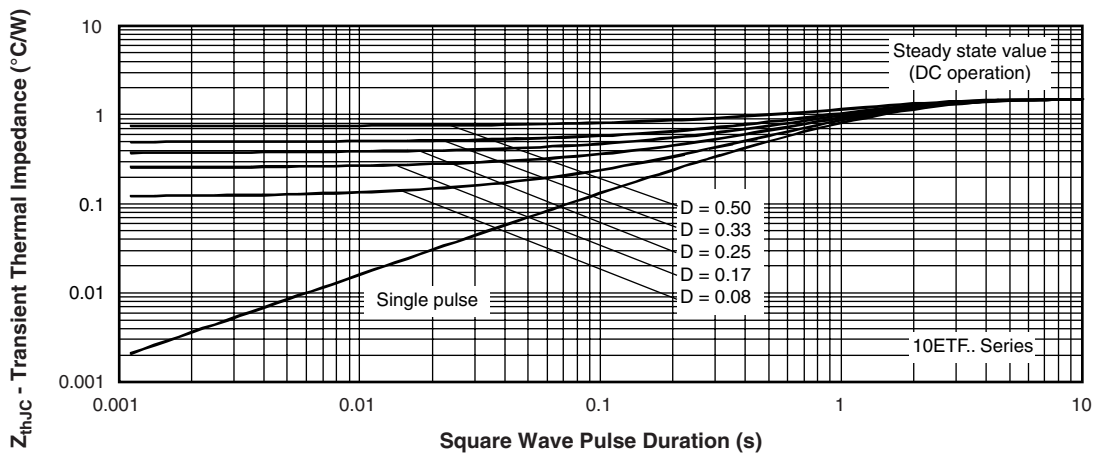
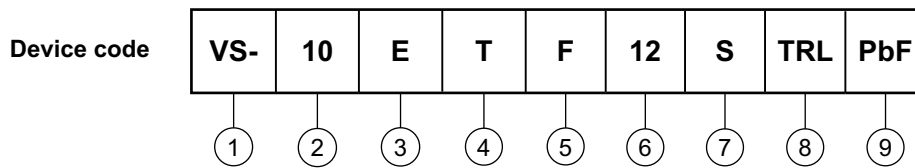


Fig. 14 - Thermal Impedance Z_{thJC} Characteristics

VS-10ETF..SPbF Soft Recovery Series



Vishay High Power Products Fast Soft Recovery
Rectifier Diode, 10 A



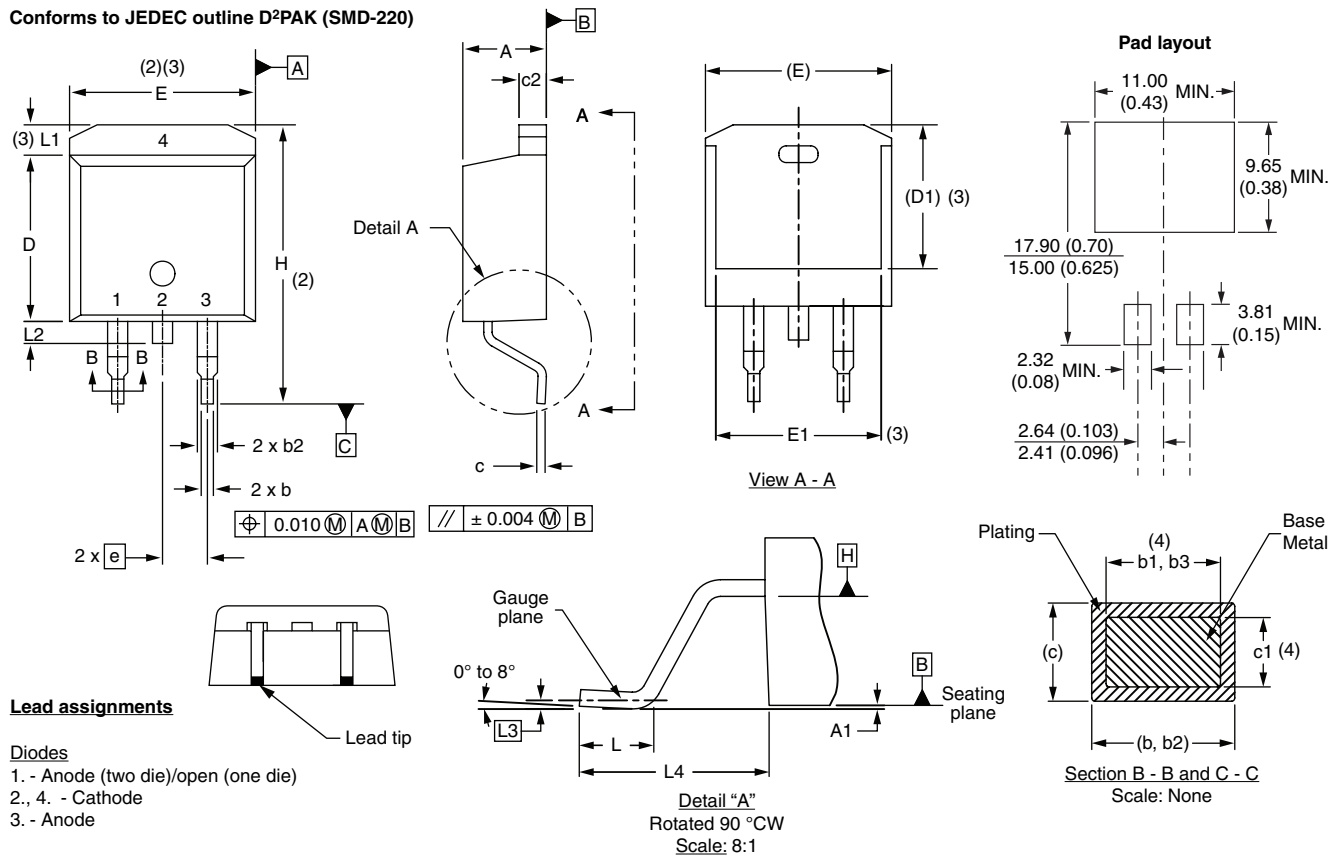
- 1** - HPP product suffix
- 2** - Current rating (10 = 10 A)
- 3** - Circuit configuration:
 - E = Single diode
- 4** - Package:
 - T = D²PAK (TO-220AC)
- 5** - Type of silicon:
 - F = Fast soft recovery rectifier
- 6** - Voltage code x 100 = V_{RRM}

10 = 1000 V
12 = 1200 V
- 7** - S = Surface mountable
- 8** -
 - None = Tube
 - TRR = Tape and reel (right oriented)
 - TRL = Tape and reel (left oriented)
- 9** - PbF = Lead (Pb)-free

D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC outline D²PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

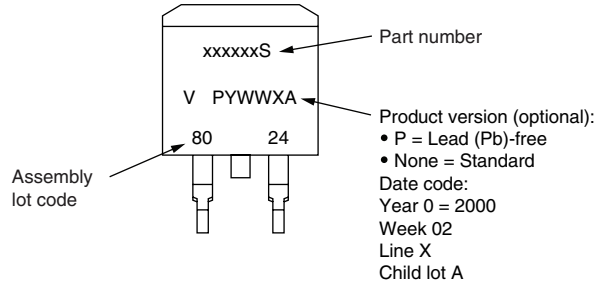
- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB



Part Marking Information

Vishay High Power Products

D²PAK



Example: This is a xxxxxxS with assembly lot code 8024, assembled on WW 02, 2000



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